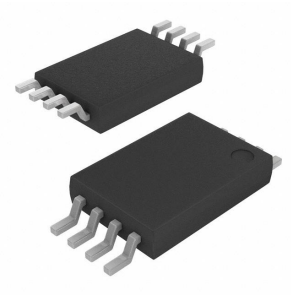
WNMD2168

Dual N-Channel, 20V, 4.1A, Power MOSFET

Http//:www.willsemi.com

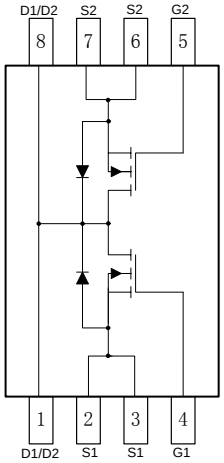
V_{DS} (V)	Rds(on) (Ω)
20	0.022@ V_{GS}=4.5V
	0.024@ V_{GS}=3.1V
	0.027@ V_{GS}=2.5V



TSSOP-8L

Descriptions

The WNMD2168 is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS\ (ON)}$ with low gate charge. This device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product WNMD2168 is Pb-free.



Pin configuration (Top view)

Features

- Trench Technology
- Supper high density cell design
- Excellent ON resistance for higher DC current
- Extremely Low Threshold Voltage
- Small package TSSOP-8L

=Logo

2168 =Device Code

YY = Year

WW = Week

Marking

Applications

- Driver for Relay, Solenoid, Motor, LED etc.
- DC-DC converter circuit
- Power Switch
- Load Switch
- Charging

Order information

Device	Package	Shipping
WNMD2168-8/TR	TSSOP-8L	3000/Reel&Tape

Absolute Maximum ratings

Parameter		Symbol	10 S	Steady State	Unit
Drain-Source Voltage		V_{DS}	+20		V
Gate-Source Voltage		V_{GS}	±10		
Continuous Drain Current [a]	T_A=25°C	I_D	5.1	4.1	A
	T_A=70°C		3.8	3.5	
Maximum Power Dissipation [a]	T_A=25°C	P_D	1.1	0.9	W
	T_A=70°C		0.7	0.6	
Continuous Drain Current [b]	T_A=25°C	I_D	4.1	3.6	A
	T_A=70°C		3.5	3.0	
Maximum Power Dissipation [b]	T_A=25°C	P_D	0.9	0.7	W
	T_A=70°C		0.55	0.45	
Pulsed Drain Current [c]		I_{DM}	25		A
Operating Junction Temperature		T_J	-55~+150		°C
Lead Temperature		T_L	260		°C
Storage Temperature Range		T_{stg}	-55~+150		°C

Thermal resistance ratings

Parameter		Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance [a]	t ≤ 10 s	$R_{\theta JA}$	87	110	°C/W
	Steady State		113	129	
Junction-to-Ambient Thermal Resistance [b]	t ≤ 10 s	$R_{\theta JA}$	102	132	
	Steady State		136	161	
Junction-to-Case Thermal Resistance	Steady State	$R_{\theta JC}$	61	75	

a Surface mounted on FR-4 Board using 1 square inch pad size, 1oz copper

b Surface mounted on FR-4 board using minimum pad size, 1oz copper

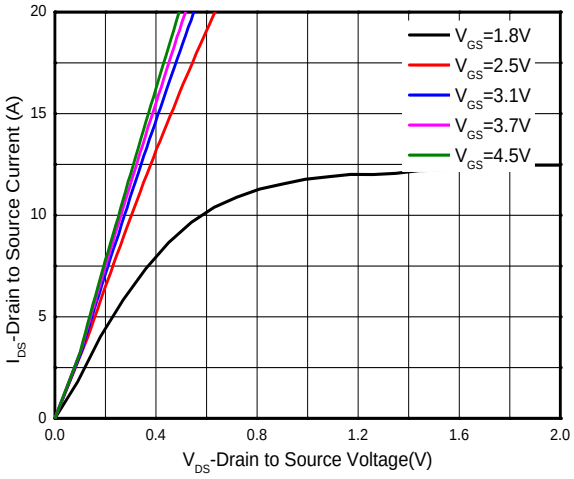
c Pulse width<380μs, Duty Cycle<2%

d Maximum junction temperature T_J=150°C.

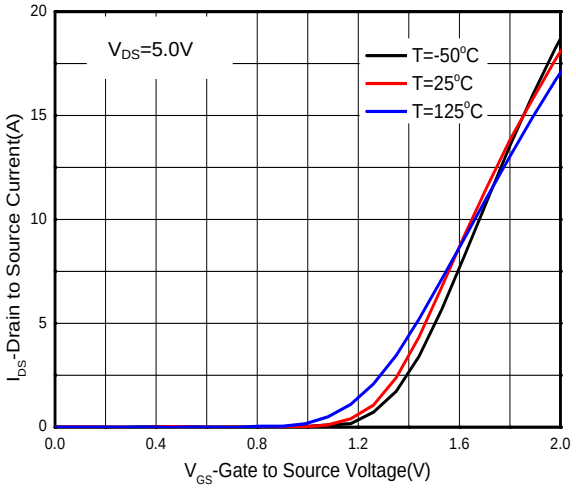
Electronics Characteristics (Ta=25°C, unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0 V, I_D = 250uA	20			V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 16V, V_{GS} = 0V			1	uA
Gate-to-source Leakage Current	I_{GSS}	V_{DS} = 0 V, V_{GS} = ±10 V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 250uA	0.45	0.75	1.0	V
Drain-to-source On-resistance [b, c]	$R_{DS(on)}$	V_{GS} = 4.5V, I_D = 4.0A	15	22	28	mΩ
		V_{GS} = 3.7V, I_D = 4.0A	17	23	30	
		V_{GS} = 3.1V, I_D = 2.5A	18	24	35	
		V_{GS} = 2.5V, I_D = 2.0A	20	27	38	
Forward Trans conductance	g_{fs}	V_{DS} = 5.0V, I_D = 4.0 A		11		S
CAPACITANCES, CHARGES						
Input Capacitance	C_{ISS}	V_{GS} = 0 V,		680		pF
Output Capacitance	C_{OSS}	f = 1.0 MHz,		95		
Reverse Transfer Capacitance	C_{RSS}	V_{DS} = 10 V		89		
Total Gate Charge	$Q_{G(TOT)}$	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 4.0A		10.8		nC
Threshold Gate Charge	$Q_{G(TH)}$			0.8		
Gate-to-Source Charge	Q_{GS}			2.3		
Gate-to-Drain Charge	Q_{GD}			2.5		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	td(ON)	V_{GS} = 4.5 V, V_{DS} = 10 V, I_D = 4.0 A, R_G=6 Ω		22		ns
Rise Time	tr			32		
Turn-Off Delay Time	td(OFF)			60		
Fall Time	tf			23		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V_{SD}	V_{GS} = 0 V, I_S = 1.0A		0.78	1.50	V

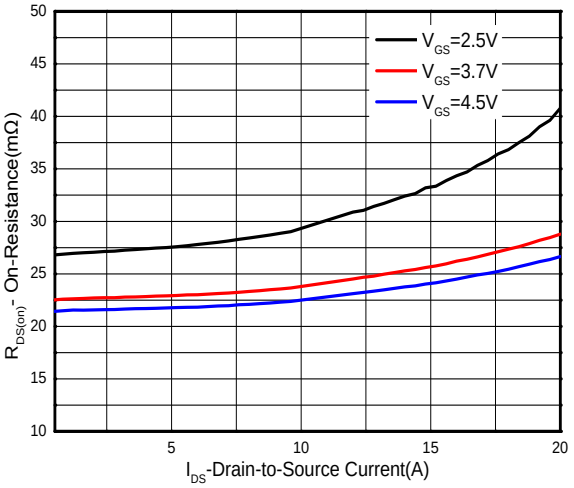
Typical Characteristics (Ta=25°C, unless otherwise noted)



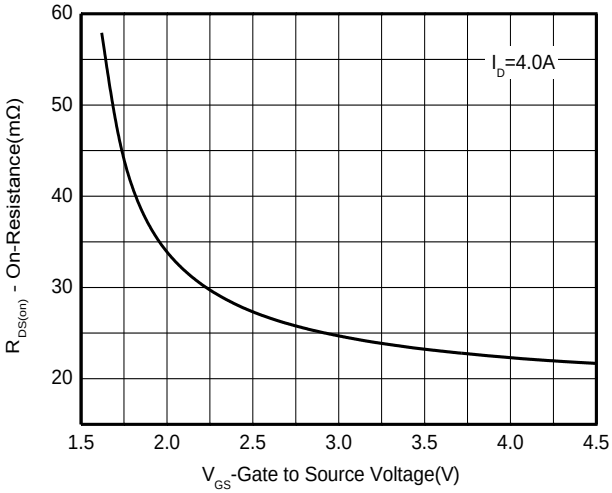
Output characteristics



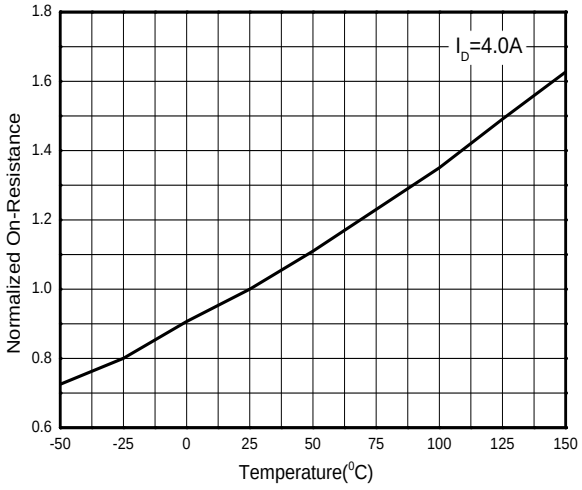
Transfer characteristics



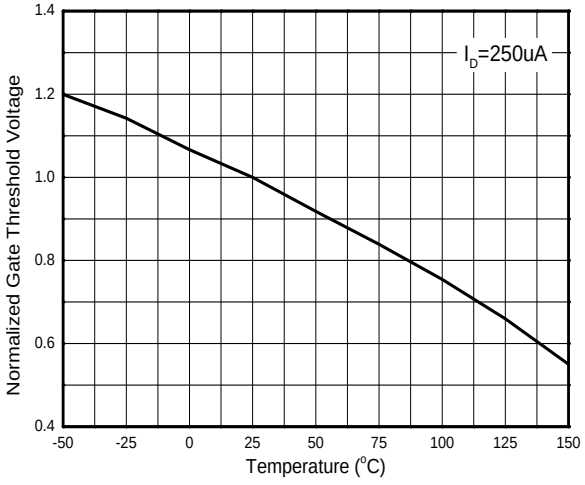
On-Resistance vs. Drain current



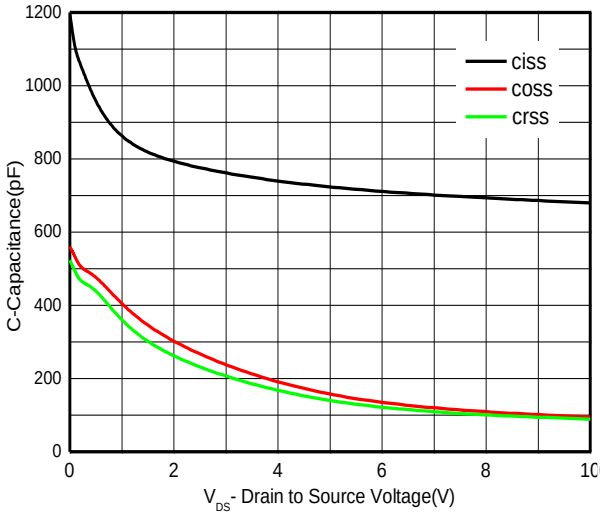
On-Resistance vs. Gate-to-Source voltage



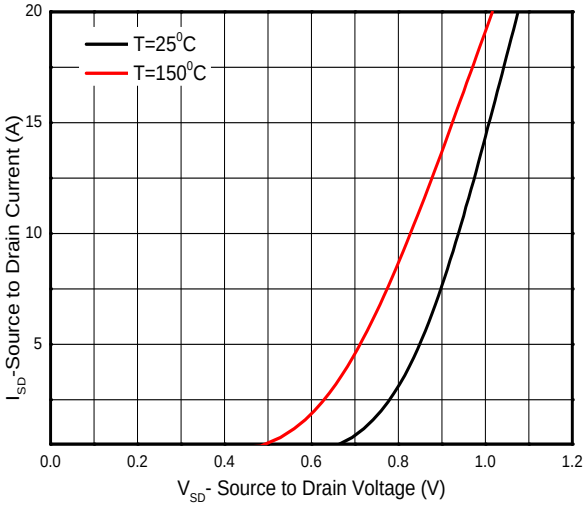
On-Resistance vs. Junction temperature



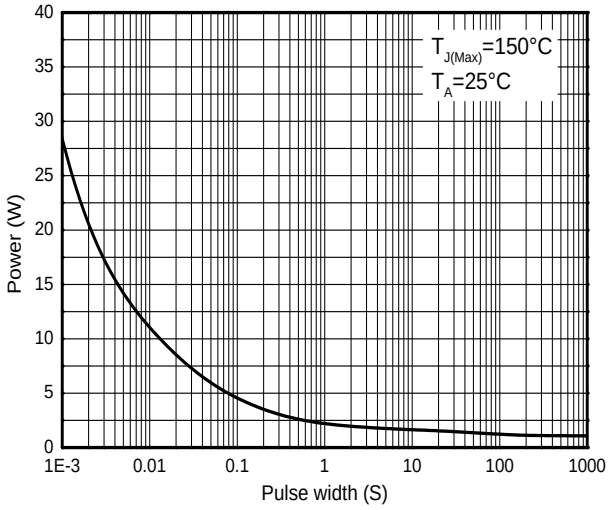
Threshold voltage vs. Temperature



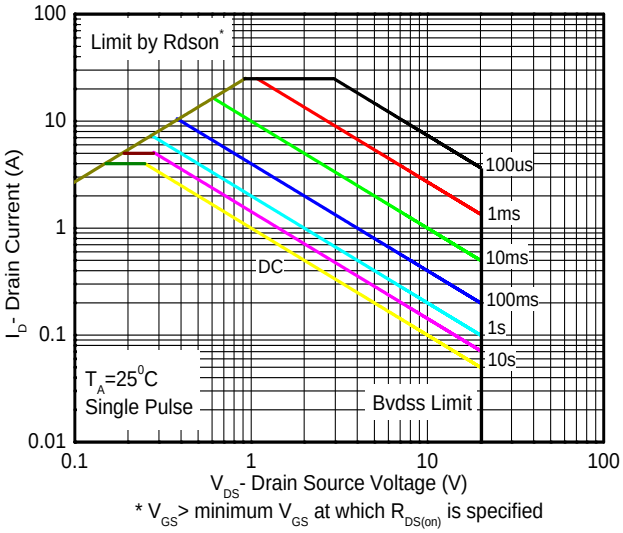
Capacitance



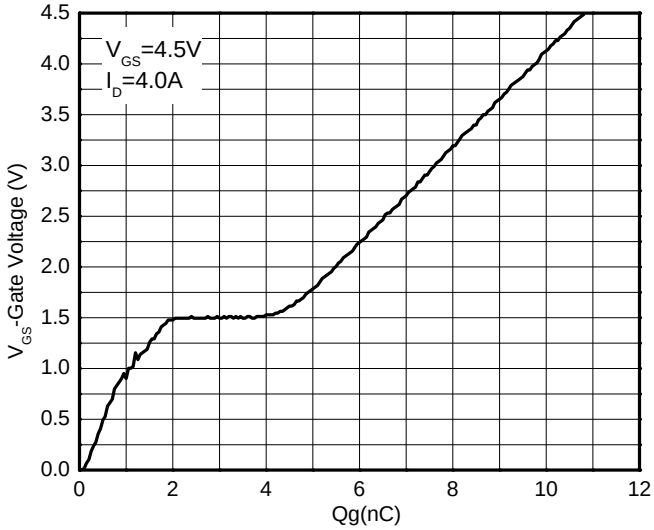
Body diode forward voltage



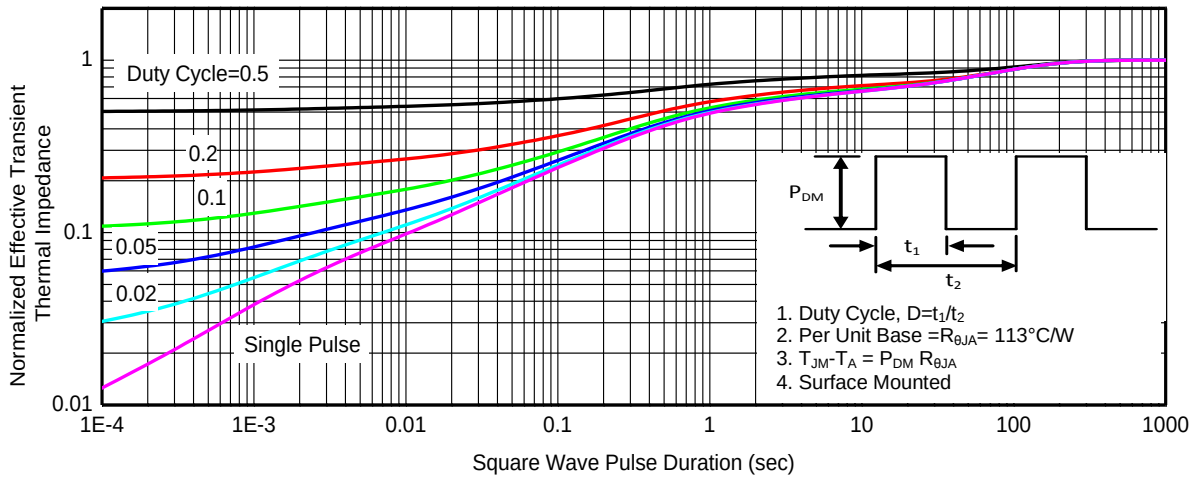
Single pulse power



Safe operating power



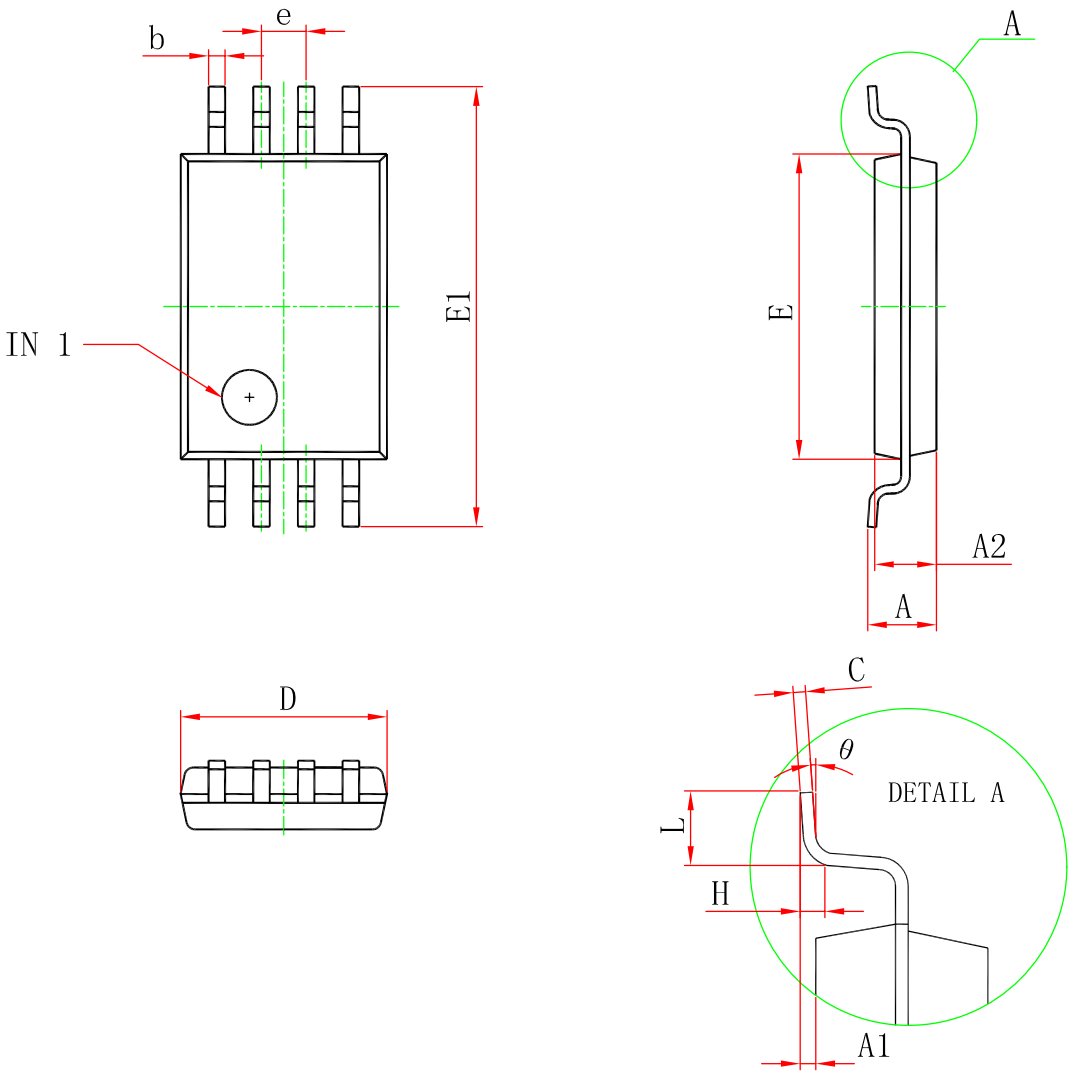
Gate charge Characteristics



Transient thermal response (Junction-to-Ambient)

Package outline dimensions

TSSOP-8L



Symbol	Dimensions in millimeter	
	Min.	Max.
D	2.900	3.100
E	4.300	4.500
b	0.190	0.300
c	0.090	0.200
E1	6.250	6.550
A		1.200
A2	0.800	1.000
A1	0.050	0.150
e	0.65(BSC)	
L	0.500	0.700
H	0.25(TYP)	
θ	1°	7°